



Mechanical data: $A_x=A_y=590\mu\text{m}$
 $B_x=B_y=350\mu\text{m}$

Chip thickness: 180+/-15

Scribe Line width - 60 μm .

Top side – pin 1: Al - metallization for wire bond.

Back side – pin 2: Ti-Ni-Ag for soldering

Schematic and pinning diagram

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Peak Pulse Power	P_{pp}	$t_p=8/20\mu\text{s}$	480*	W
Peak Pulse Current	I_{pp}	$t_p=8/20\mu\text{s}$	40,0*	A
Electrostatic discharge	VESD	IEC 61000-4-2. Level-4. Pin1 to Pin2.	+30,0-Contact. +30,0-Air.	kV
Max .junction temperature	T_j	-	+125	°C

Characteristics (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{rwm}	Reverse Stand-off voltage		-	-	2,5	V
V_{pt}	Punch-Through Voltage.	$I_{pt}=2\mu\text{A}$	2,8**	-	-	V
V_{sb}	Snap-Back Voltage.	$I_{sb}=50\text{mA}$	2,5	-	4,0	V
I_r	Reverse leakage current	$V_R=2,8\text{V}$; "+" on pin 1	-	-	0,2	μA
C_j	Diode capacitance .	$F=1\text{MHz}$, $V_{dc}=0\text{V}$.	-	85	-	pF
V_{CL}	Clamping voltage	$I_R=1\text{A}$, $t_p=8/20\mu\text{S}$ $I_R=10,0\text{A}$, $t_p=8/20\mu\text{S}$ $I_R=25,0\text{A}$, $t_D=8/20\mu\text{S}$	-	-	4,2* 5,5* 7,5*	V
*- For Device testing. **- This Parameter guaranteed for Device.						